上海贝岭 SHANGHAI BELLING

BLM40P10

Power MOSFET

1. Description

➢ Advantages

BLM40P10 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

➢ Key Characteristics

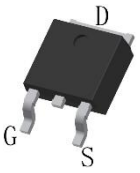
Parameter	Value	Unit
V_{DS}	-100	V
I_D	-35	A
$R_{DS(ON).Typ}$	35	mΩ

➢ Features

- High power and current handing capability
- Lead free product is acquired
- 100% avalanche tested
- RoHS product

➢ Applications

- Load switch
- Power management



TO-252 Top View

TO-220 Top View

➢ Ordering Informations

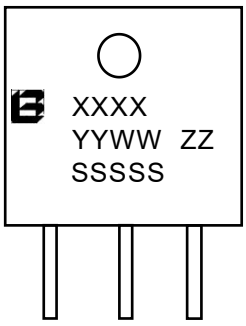
Device Marking	Ordering Codes	Package	Product Code	Packing
M40P10	BLM40P10-D	TO-252	BLM40P10	Reel
M40P10	BLM40P10-P	TO-220	BLM40P10	Tube

BLM40P10-D,P

(2) Package type

(1) Chip name

(1)BLM40P10:-100V 42mΩ
(2)D:TO-252 P:TO-220



XXXX：Device Marking

YYWW：Year&Week

ZZ：Assembly Code

SSSSS：Lot Code

2. Absolute Ratings

at T_C = 25°C, unless otherwise specified

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	-100	V
I_D	Continuous Drain Current	-35	A
	Continuous Drain Current T_C = 100 °C	-23	A
I_{DM}	Pulsed Drain Current(Note1)	-220	A
P_D	Power Dissipation	125	W
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS}	Single Pulse Avalanche Energy(Note2)	100	mJ
T_J， T_{stg}	Operating Junction and Storage Temperature Range	150，-55 to 150	℃

3. Thermal Characteristics

Symbol	Parameter	Rating	Units
$R_{\theta JC}$	Junction-to-Case	1.1	℃/W

4. Electrical Characteristics

at T_C = 25°C, unless otherwise specified

OFF Characteristics						
Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	V_{GS}=0V, I_D=-250μA	-100	--	--	V
I_{DSS}	Drain to Source Leakage Current	V_{DS} =-100V, V_{GS}= 0V, T_j= 25℃	--	--	1	μA
I_{GSS}	Gate to Source Forward Leakage	V_{GS} =±20V	--	--	± 100	nA

ON Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	V_{GS}=-10V, I_D=-30A(Note3)	--	35	42	mΩ
		V_{GS}=-4.5V, I_D=-30A(Note3)	--	42	50	mΩ
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D =-250μA(Note3)	-1	-1.5	-2.5	V

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
R_g	Gate resistance	f = 1.0MHz	--	8.3	--	Ω
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = -25V f = 1.0MHz	--	4225	--	pF
C_{oss}	Output Capacitance		--	190	--	
C_{rss}	Reverse Transfer Capacitance		--	165	--	

Switching Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	I_D = -15A V_{DD} = -50V V_{GS} = -10V R_G =9Ω	--	18	--	ns
t_r	Rise Time		--	80	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	45	--	
t_f	Fall Time		--	65	--	
Q_g	Total Gate Charge	I_D = -30A V_{DS} = -50V V_{GS} = -10V	--	93	--	nC
Q_{gs}	Gate to Source Charge		--	15	--	
Q_{gd}	Gate to Drain (“Miller”)Charge		--	18	--	

Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)	T_C = 25 °C	--	--	-35	A
V_{SD}	Diode Forward Voltage	I_S = -2.5A, V_{GS} = 0V(Note3)	--	--	-1.2	V

Note1: Pulse width limited by maximum junction temperature

Note2: Eas condition：Vg=-10V,L=0.5mH, Vds=-50V, Start TJ=25℃, Ias=-20A

Note3: Pulse width tp≤300μs, δ≤2%

5. Characteristics Curves

Figure 1 Output Characteristics

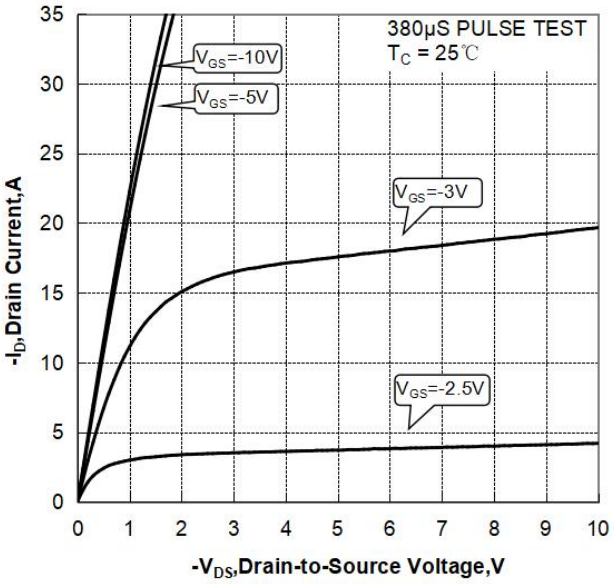


Figure 2 Transfer Characteristics

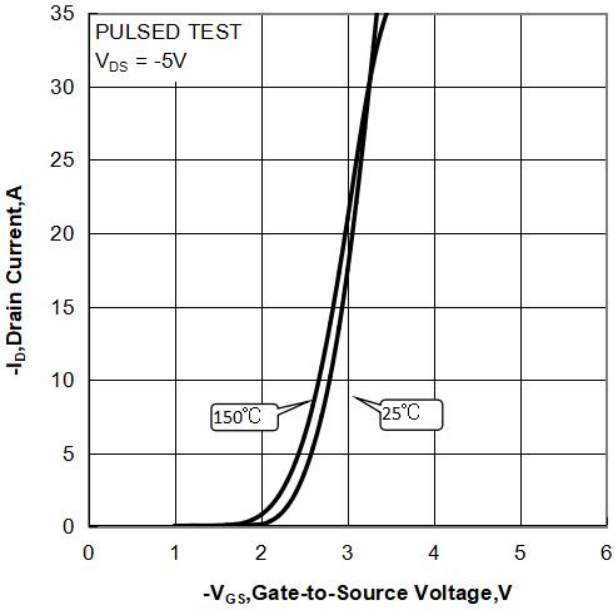


Figure 3 On-Resistance vs. I_D

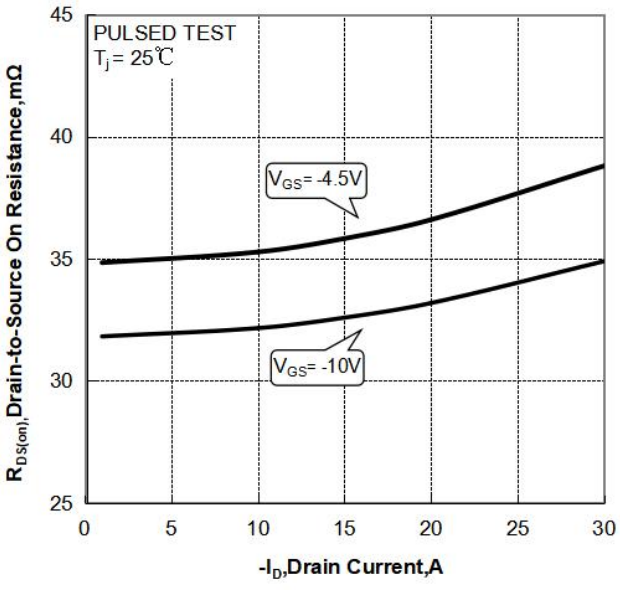


Figure 4 On-Resistance vs. Junction Temperature

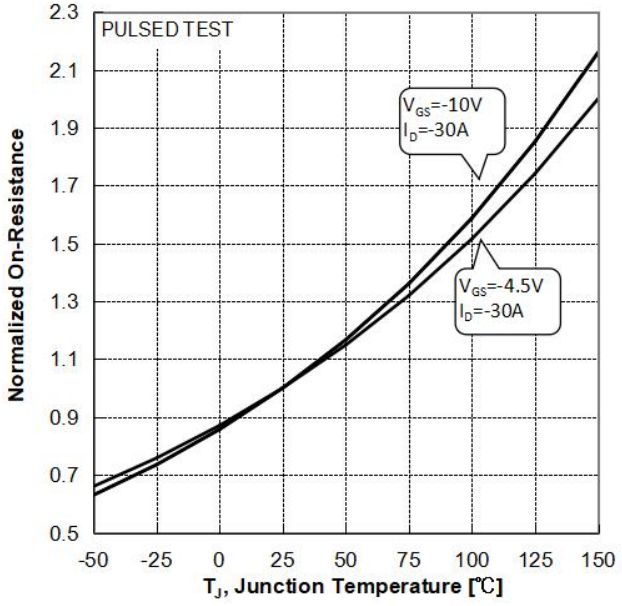


Figure 5 BV vs Junction Temperature

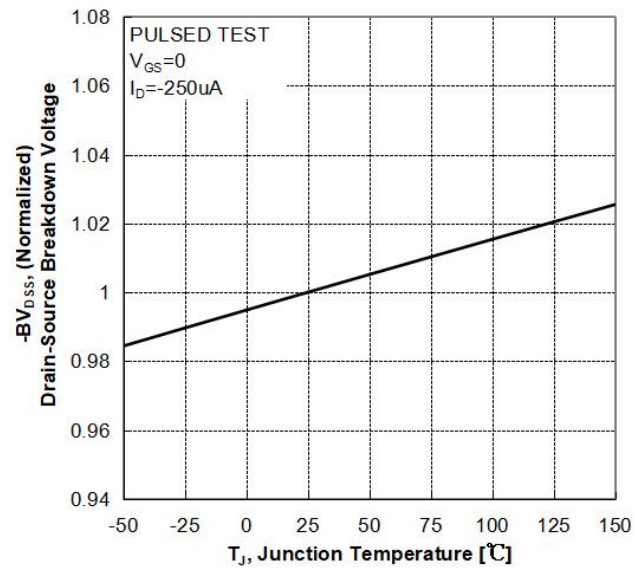


Figure 6 Vth vs Junction Temperature

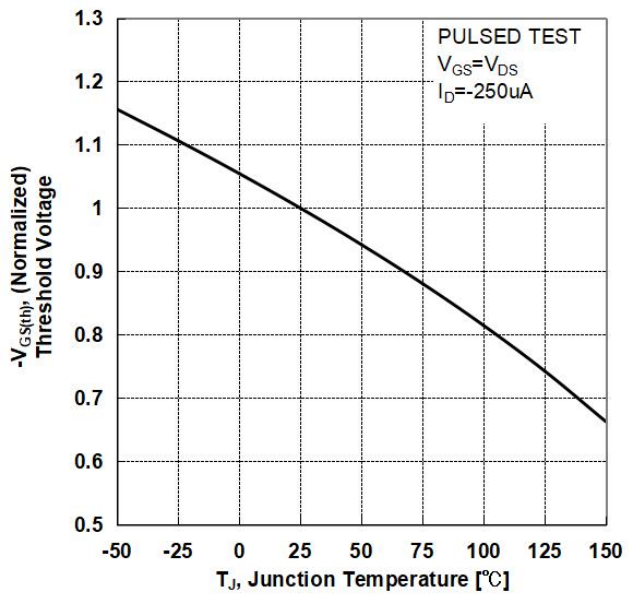


Figure 7 Gate-Charge Characteristics

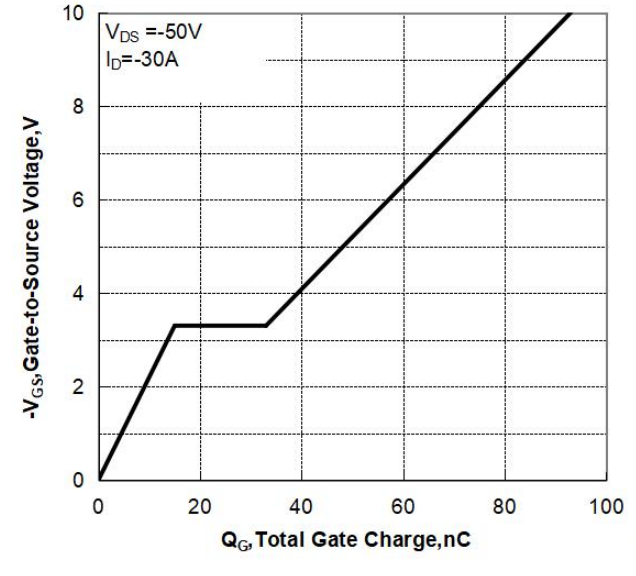


Figure 8 Capacitance Characteristics

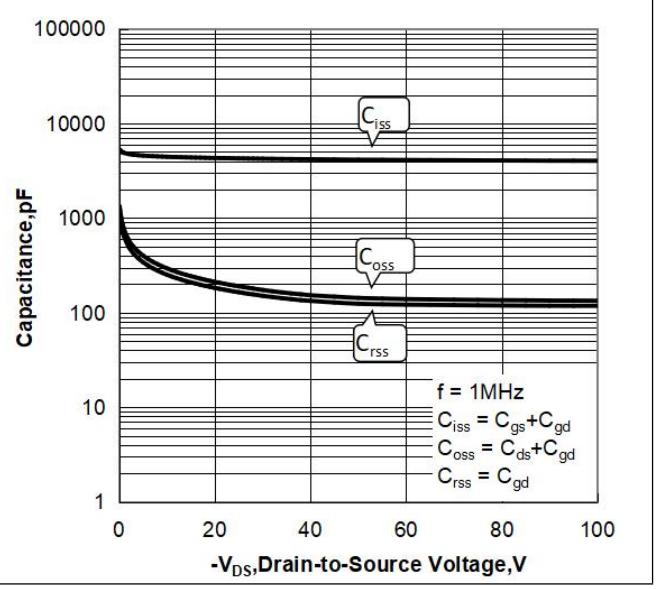


Figure 9 Body Diode Forward Voltage

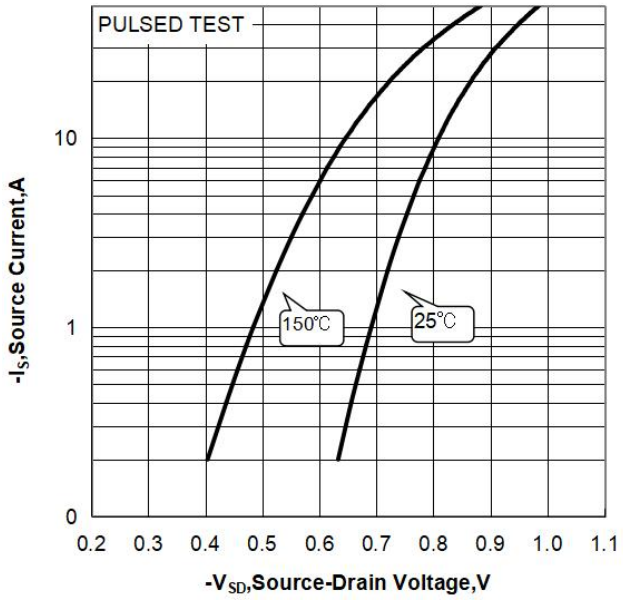


Figure 10 Maximum Safe Operating Area

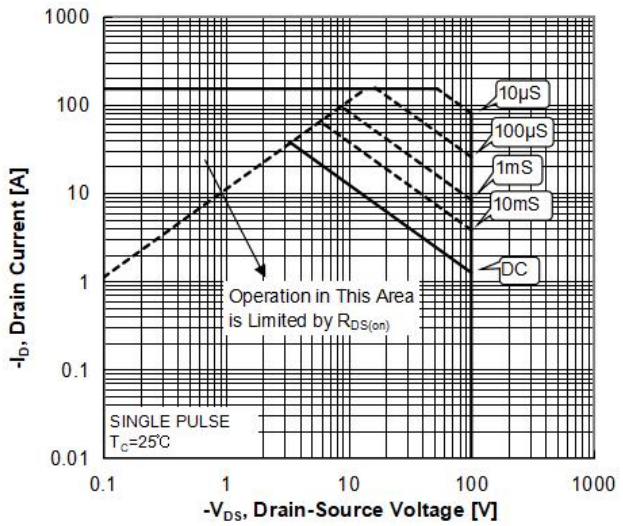
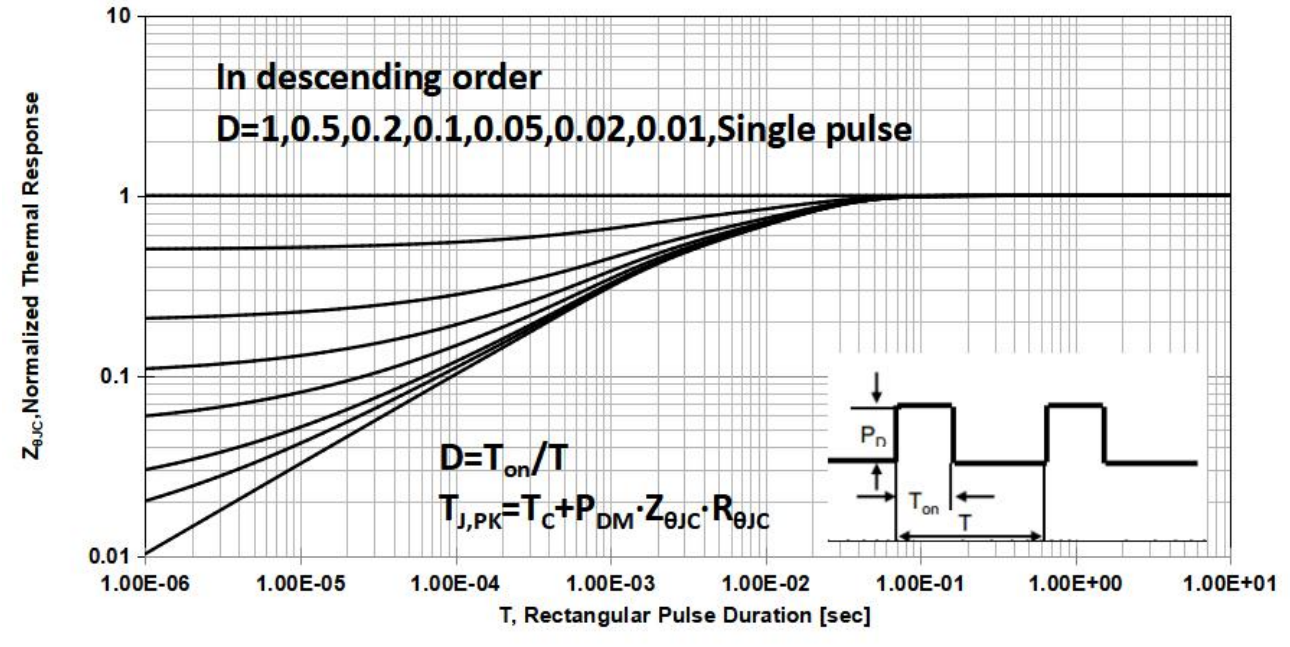
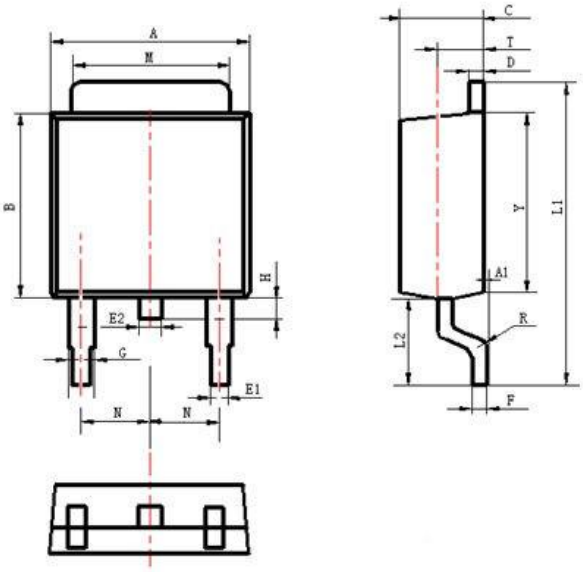


Figure 11 Transient Thermal Impedance

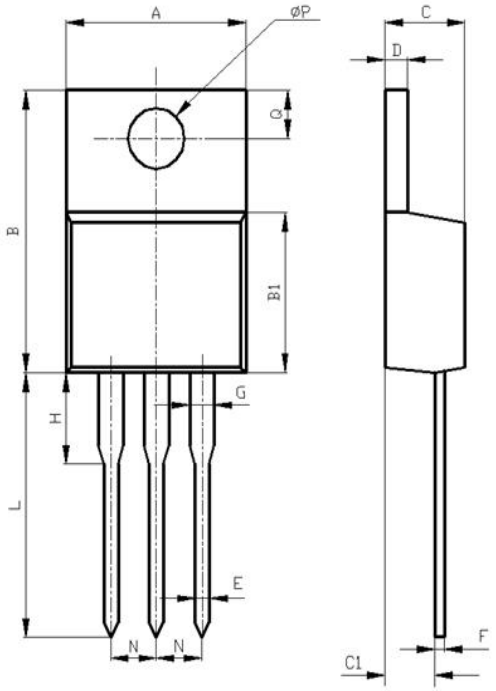


6. Package Description



Items	Values(mm)	
	MIN	MAX
A	6.30	6.90
A1	0	0.13
B	5.70	6.30
C	2.10	2.50
D	0.30	0.60
E1	0.60	0.90
E2	0.70	1.00
F	0.30	0.60
G	0.70	1.20
L1	9.60	10.50
L2	2.70	3.10
H	0.60	1.00
M	5.10	5.50
N	2.09	2.49
R	0 .3	
T	1.40	1.60
Y	5.10	6.30

TO-252-2L Package



Items	Values(mm)	
	MIN	MAX
A	9.60	10.6
B	15.0	16.0
B1	8.90	9.50
C	4.30	4.80
C1	2.30	3.10
D	1.20	1.40
E	0.70	0.90
F	0.30	0.60
G	1.17	1.37
H	2.70	3.80
L	12.6	14.8
N	2.34	2.74
Q	2.40	3.00
ΦP	3.50	3.90

TO-220 Package

NOTE:

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. MOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. Shanghai Belling reserves the right to make changes in this specification sheet and is subject to change without prior notice.

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